Dielectric Property of Single Crystalline BaTi$_2$O$_5$ Prepared by a Floating Zone Method

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Single crystalline BaTi$_2$O$_5$ was prepared by a floating zone method. The permittivity of single crystalline BaTi$_2$O$_5$ perpendicular to a (010) plane showed the maximum value of 20500 at 748 K obeying the Curie-Weiss law at higher temperatures. The permittivity perpendicular to (100) and (001) planes were 140 and 70, respectively almost independent of temperature. A transition temperature measured by a dilatometer showed the maximum value of 748 K. The crystal structure and thermal stability of BaTi$_2$O$_5$ was prepared by a floating zone method. The permittivity of single crystalline BaTi$_2$O$_5$ perpendicular to a (010) plane was 1/2. The mixed powders were isostatically pressed at 10 MPa in a latex tube with 10 mm in diameter, and sintered at 1503 K for 43 ks in air. The sintered single crystals were stable even at several times greater than those of BaTiO$_3$.

1. Introduction

BaO–TiO$_2$ system compounds are intriguing materials for many dielectric applications. BaTiO$_3$ in particular has been widely applied to capacitors and actuators due to excellent ferroelectricity and positive temperature coefficient (PTC). TiO$_2$ rich BaO–TiO$_2$ system compounds such as BaTi$_2$O$_5$ and Ba$_4$Ti$_5$O$_{12}$ are also exhibited attractive dielectric properties such as low dielectric loss and high dielectric constant at microwave frequencies. However, BaTi$_2$O$_5$ has not been investigated in detail as a dielectric material.

The crystal structure and thermal stability of BaTi$_2$O$_5$ were studied in the past. Rase et al. showed BaTi$_2$O$_5$ in a phase diagram as a stable phase. Then, Negas et al. and O’Bryan, Jr. et al. reported that the BaTi$_2$O$_5$ phase was metastable at temperatures below a solidus line, because it decomposed to BaTiO$_3$ and Ba$_4$Ti$_7$O$_{12}$ phase. Therefore, BaTi$_2$O$_5$ phase was not indicated in phase diagrams by Negas et al. and O’Bryan, Jr. et al. and Kelvin et al. On the other hand, Ritter et al. reported that BaTi$_2$O$_5$ was stable at low temperatures below 1420 K. Pfaff reported that the BaTi$_2$O$_5$ phase synthesized by a sol-gel method had a permittivity around 40 at room temperature. However, no paper has mentioned the temperature dependence of permittivity and electrical conductivity of BaTi$_2$O$_5$.

We reported that single crystalline BaTi$_2$O$_5$ prepared by a floating zone method had a high permittivity and Ba$_4$Ti$_7$O$_{12}$ single crystals were dark blue due to slightly oxygen deficient composition, because they became transparent after a heat treatment at 1503 K in air for 3.6 ks. The BaTi$_2$O$_5$ single crystals were stable even after a heat treatment at 1523 K for 173 ks, although BaTi$_2$O$_5$ powder was decomposed to BaTiO$_3$ and Ba$_4$Ti$_7$O$_{12}$ at 1503 K.

Figure 1 shows the frequency dependence of permittivity for single crystalline BaTi$_2$O$_5$ perpendicular to a (010) plane. The permittivity decreased with increasing frequency, and became almost constant over 1 MHz. Figure 2 shows the temperature dependence of permittivities perpendicular to (100), (010) and (001) planes at 1 MHz. The permittivity perpendicular to the (010) plane showed the sharp maximum at 748 K. The maximum value (\(\epsilon = 20500\) at 748 K) was several times greater than those of BaTiO$_3$ (\(\epsilon = 7600\) at 400 K) and Bi$_4$Ti$_3$O$_{12}$ (\(\epsilon = 600\) at 940 K).
tivities perpendicular to the (100) and (001) planes were about 140 and 70, respectively, almost independent of temperature. Figure 3 shows the relationship between reciprocal permittivity and temperature perpendicular to the (010) plane. The temperature dependence of permittivity obeyed the Curie-Weiss law at higher temperatures. The Curie-Weiss temperature was calculated to be 747 K.

Figure 4 shows the polarization ($P$) vs. electric field ($E$) plots perpendicular to (100), (010) and (001) planes at room temperature. The $P$–$E$ plot perpendicular to the (010) plane showed hysteresis indicating ferroelectricity. No hysteresis was observed in the directions perpendicular to (100) and (001) planes. The remanent polarization and coercive electric field at room temperature were $1.92 \times 10^{-2}$ Cm$^{-2}$ and $2.44 \times 10^5$ Vm$^{-1}$, respectively.

The space group of BaTi$_2$O$_5$ has been reported to be $C2/m$,6,14) which has a mirror plane parallel to a (010) plane. The space group of $C2/m$, however, disagrees with the ferroelectricity perpendicular to a (010) plane. Therefore, we conclude that the space group is $C21$ and the ferroelectricity results from the shift of Ba$^{2+}$ and Ti$^{4+}$ ions to (010) direction. Ferroelectricity did not observed perpendicular to (100) and (001) planes because of two-fold symmetry in a $ac$ plane. Figure 5 shows the $P$–$E$ plots perpendicular to the (010) plane at high temperatures. The hysteresis loops became larger with increasing temperature, and the polarization was almost saturated at 523 K. The remanent polarization and coercive electric field at 523 K were $10.4 \times 10^{-2}$ Cm$^{-2}$ and $2.69 \times 10^5$ Vm$^{-1}$, respectively.

Figure 6 shows the thermal expansion of single crystalline BaTi$_2$O$_5$ perpendicular to a (010) plane. With increasing temperature, the thermal expansion coefficient was changed around 750 K. No hysteresis of thermal expansion was observed with increasing and decreasing temperature. The temperature where the thermal expansion coefficient changed was in good agreement with that of highest permittivity, indicating a ferroelectric phase transition.

Figure 7 shows the electrical conductivities perpendicular to (100), (010) and (001) planes. The electrical conductivities in these directions were smaller than that of polycrystalline...
BaTiO$_3$. The electrical conductivity perpendicular to the (010) was larger than those of (100) and (001) planes. The activation energy of electrical conductivity of BaTi$_2$O$_5$ was 147 to 180 kJ mol$^{-1}$ independent of directions and higher than that of BaTiO$_3$. This may cause the higher activation energy than that of BaTiO$_3$.

4. Conclusion

The single crystalline BaTi$_2$O$_5$ has a maximum permittivity of 20500 at 748 K perpendicular to a (010) plane. The temperature dependence of permittivity perpendicular to a (010) plane obeyed the Curie-Weiss law at higher temperatures. The $P$–$E$ hysteresis loops indicated a ferroelectricity perpendicular to a (010) plane at lower temperatures, but no hysteresis was observed perpendicular to (100) and (001) planes. The ferroelectric phase transition temperature by AC impedance measurements was in good agreement with that by a dilatometer. The electrical conductivity perpendicular to the (010) was larger than those of (100) and (001) planes. The activation energy of electrical conductivity was almost independent of directions.

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REFERENCES